

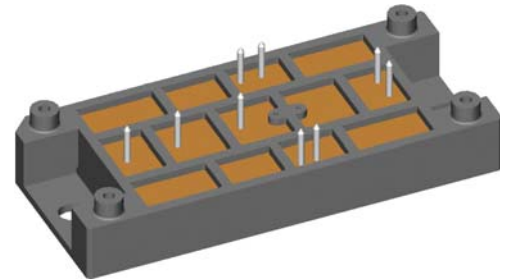
Standard Rectifier Module

3~ Rectifier
$V_{RRM} = 1200\text{ V}$
$I_{DAV} = 180\text{ A}$
$I_{FSM} = 1100\text{ A}$

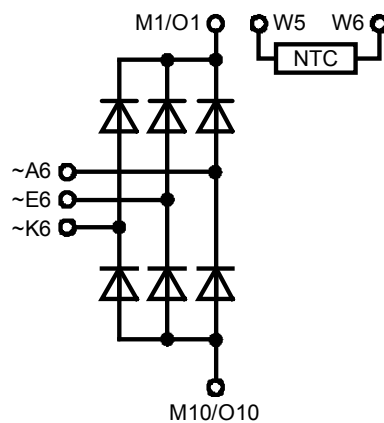
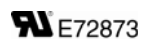
3~ Rectifier Bridge + NTC

Part number

VUO120-12NO2T



Backside: isolated



Features / Advantages:

- Package with DCB ceramic
- Reduced weight
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current
- NTC

Applications:

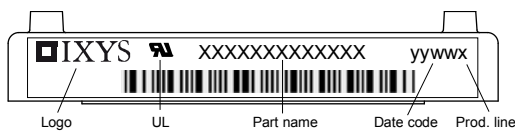
- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: V2-Pack

- Isolation Voltage: 3600V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 17 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					1300	V
V_{RRM}	max. repetitive reverse blocking voltage					1200	V
I_R	reverse current	$V_R = 1200$ V	$T_{VJ} = 25^\circ\text{C}$			100	μA
		$V_R = 1200$ V	$T_{VJ} = 125^\circ\text{C}$			2	mA
V_F	forward voltage drop	$I_F = 60$ A	$T_{VJ} = 25^\circ\text{C}$			1.16	V
		$I_F = 180$ A				1.55	V
		$I_F = 60$ A	$T_{VJ} = 125^\circ\text{C}$			1.09	V
		$I_F = 180$ A				1.59	V
I_{DAV}	bridge output current	$T_C = 90^\circ\text{C}$	$T_{VJ} = 150^\circ\text{C}$			180	A
		rectangular	$d = \frac{1}{3}$				
V_{FO}	threshold voltage	} for power loss calculation only				0.81	V
r_F	slope resistance					4.4	m Ω
R_{thJC}	thermal resistance junction to case					0.6	K/W
R_{thCH}	thermal resistance case to heatsink				0.2		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		205	W
I_{FSM}	max. forward surge current	$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			1.10	kA
		$t = 8,3$ ms; (60 Hz), sine	$V_R = 0$ V			1.19	kA
		$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			935	A
		$t = 8,3$ ms; (60 Hz), sine	$V_R = 0$ V			1.01	kA
I^2t	value for fusing	$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 45^\circ\text{C}$			6.05	kA ² s
		$t = 8,3$ ms; (60 Hz), sine	$V_R = 0$ V			5.89	kA ² s
		$t = 10$ ms; (50 Hz), sine	$T_{VJ} = 150^\circ\text{C}$			4.37	kA ² s
		$t = 8,3$ ms; (60 Hz), sine	$V_R = 0$ V			4.25	kA ² s
C_J	junction capacitance	$V_R = 400$ V; $f = 1$ MHz	$T_{VJ} = 25^\circ\text{C}$		37		pF

Package V2-Pack		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			100	A
T_{stg}	storage temperature		-40		125	°C
T_{VJ}	virtual junction temperature		-40		150	°C
Weight				76		g
M_D	mounting torque		2		2.5	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	12.0			mm
V_{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute 50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	3000			V



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO120-12NO2T	VUO120-12NO2T	Box	6	510989

Similar Part	Package	Voltage class
VUO120-16NO2T	V2-Pack	1600

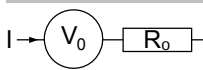
Temperature Sensor NTC

Symbol	Definition	Conditions	min.	typ.	max.	Unit
R_{25}	resistance	$T_{VJ} = 25^\circ$	4.75	5	5.25	k Ω
$B_{25/50}$	temperature coefficient			3375		K

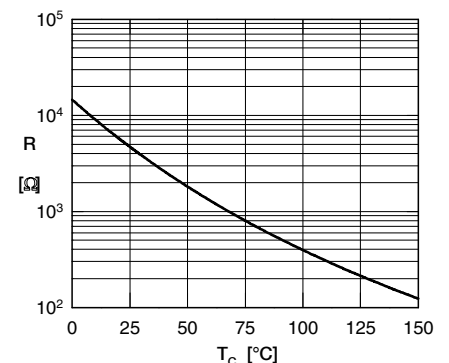
Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^\circ\text{C}$



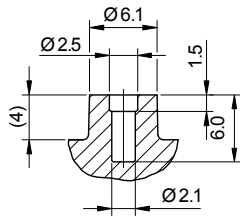
$V_{0\max}$	threshold voltage	0.81				V
$R_{0\max}$	slope resistance *	3.2				m Ω



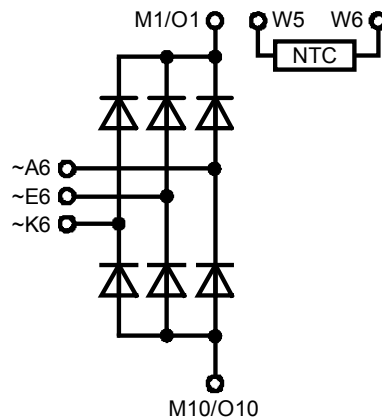
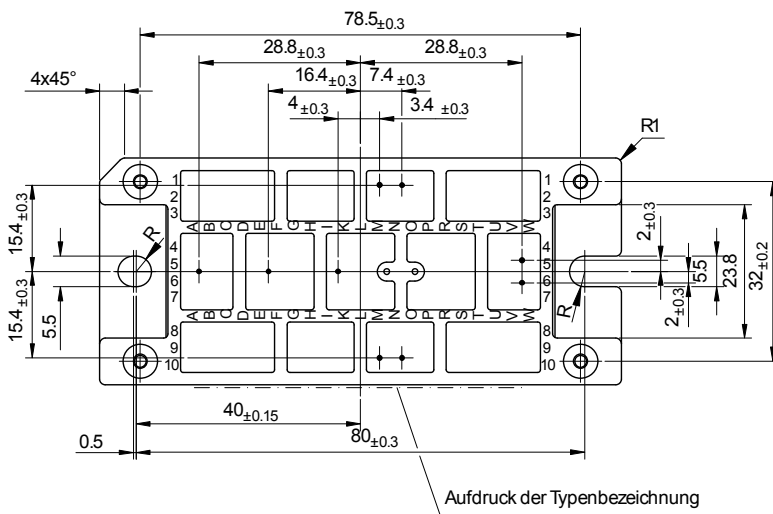
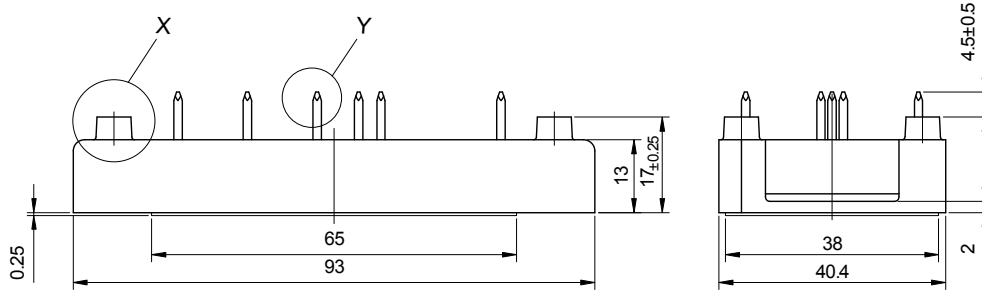
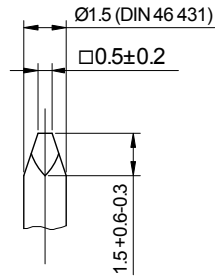
Typ. NTC resistance vs. temperature

Outlines V2-Pack

Detail X M2:1



Detail Y M5:1



Rectifier

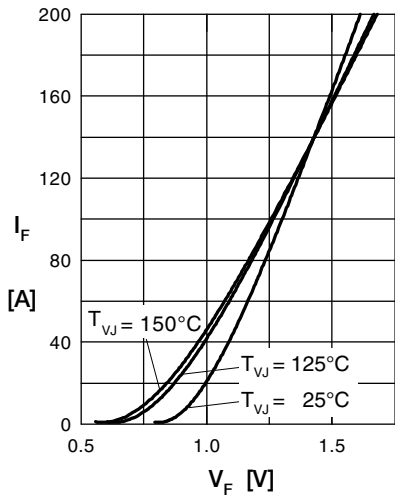


Fig. 1 Forward current vs. voltage drop per diode

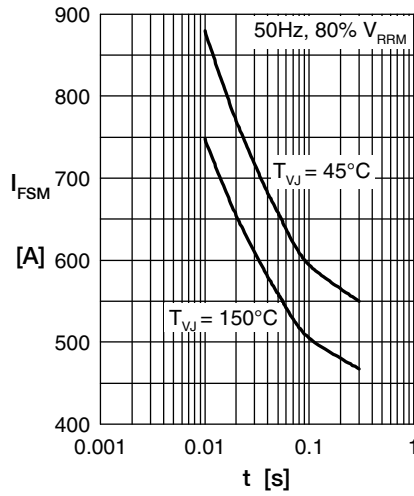


Fig. 2 Surge overload current vs. time per diode

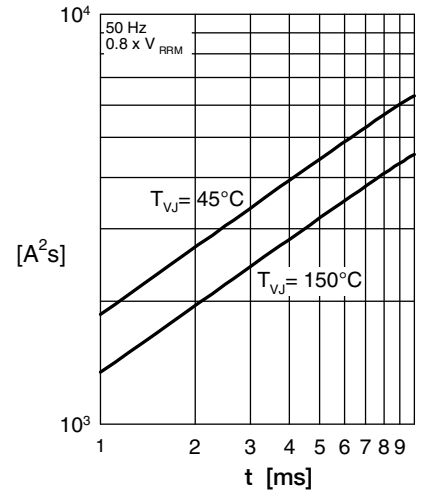


Fig. 3 I^2t vs. time per diode

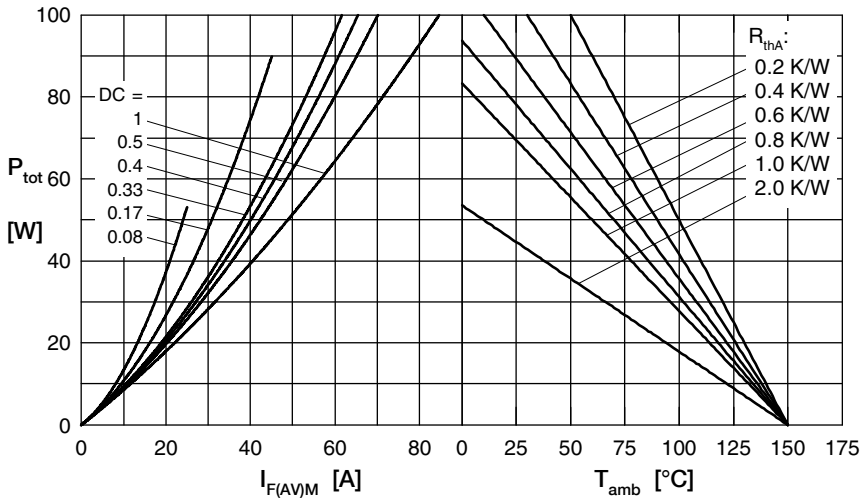


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

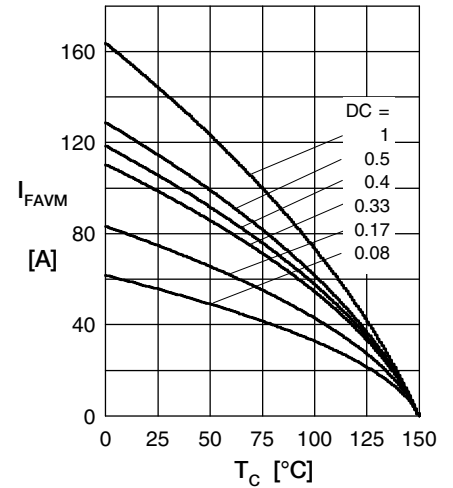


Fig. 5 Max. forward current vs. case temperature per diode

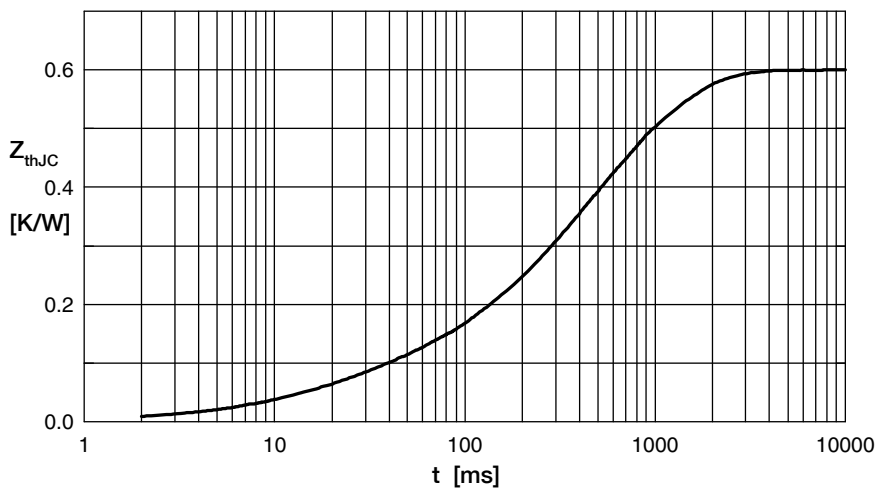


Fig. 6 Transient thermal impedance junction to case vs. time per diode